

N-Channel NexFET™ Power MOSFET

 Check for Samples: [CSD16322Q5](#)

FEATURES

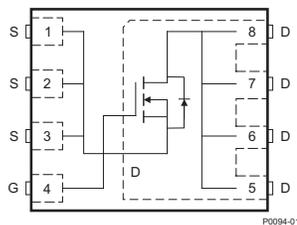
- Optimized for 5V Gate Drive
- Ultralow Q_g and Q_{gd}
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 5-mm x 6-mm Plastic Package

APPLICATIONS

- Point-of-Load Synchronous Buck in Networking, Telecom and Computing Systems
- Synchronous or Control FET Applications

DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications and optimized for 5V gate drive applications.

Top View


PRODUCT SUMMARY

V_{DS}	Drain to Source Voltage	25	V
Q_g	Gate Charge Total (4.5V)	6.8	nC
Q_{gd}	Gate Charge Gate to Drain	1.3	nC
$R_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 3V$	5.4 mΩ
		$V_{GS} = 4.5V$	4.6 mΩ
		$V_{GS} = 8V$	3.9 mΩ
$V_{GS(th)}$	Threshold Voltage	1.1	V

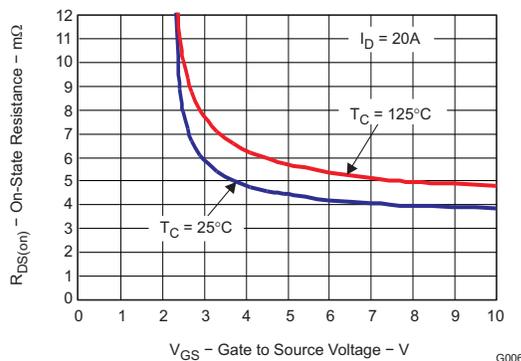
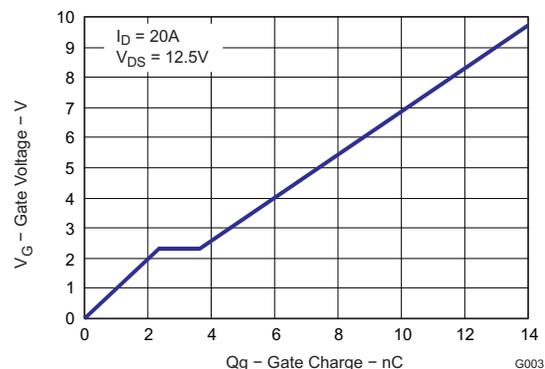
ORDERING INFORMATION

Device	Package	Media	Qty	Ship
CSD16322Q5	SON 5-mm x 6-mm Plastic Package	13-Inch Reel	2500	Tape and Reel

ABSOLUTE MAXIMUM RATINGS

$T_A = 25^\circ\text{C}$ unless otherwise stated		VALUE	UNIT
V_{DS}	Drain to Source Voltage	25	V
V_{GS}	Gate to Source Voltage	+10 / -8	V
I_D	Continuous Drain Current, $T_C = 25^\circ\text{C}$	97	A
	Continuous Drain Current ⁽¹⁾	21	A
I_{DM}	Pulsed Drain Current, $T_A = 25^\circ\text{C}$ ⁽²⁾	136	A
P_D	Power Dissipation ⁽¹⁾	3.1	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 to 150	$^\circ\text{C}$
E_{AS}	Avalanche Energy, single pulse $I_D = 50A, L = 0.1mH, R_G = 25\Omega$	125	mJ

- (1) Typical $R_{\theta JA} = 39^\circ\text{C/W}$ on 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 0.06-inch (1.52-mm) thick FR4 PCB.
- (2) Pulse duration $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$

 $R_{DS(on)}$ VS V_{GS}

GATE CHARGE


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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

($T_A = 25^\circ\text{C}$ unless otherwise stated)

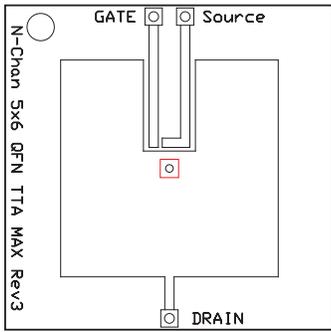
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Characteristics						
BV_{DSS}	Drain to Source Voltage	$V_{GS} = 0V, I_D = 250\mu A$	25			V
I_{DSS}	Drain to Source Leakage Current	$V_{GS} = 0V, V_{DS} = 20V$			1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{DS} = 0V, V_{GS} = +10/-8V$			100	nA
$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.9	1.1	1.4	V
$R_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 3V, I_D = 20A$		5.4	7.2	m Ω
		$V_{GS} = 4.5V, I_D = 20A$		4.6	5.8	m Ω
		$V_{GS} = 8V, I_D = 20A$		3.9	5	m Ω
g_{fs}	Transconductance	$V_{DS} = 15V, I_D = 20A$		106		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{GS} = 0V, V_{DS} = 12.5V,$ $f = 1MHz$	1050	1365		pF
C_{oss}	Output Capacitance		740	950		pF
C_{rss}	Reverse Transfer Capacitance		55	70		pF
R_G	Series Gate Resistance		1.1	2.2		Ω
Q_g	Gate Charge Total (4.5V)	$V_{DS} = 12.5V,$ $I_D = 20A$	6.8	9.7		nC
Q_{gd}	Gate Charge Gate to Drain		1.3			nC
Q_{gs}	Gate Charge Gate to Source		2.4			nC
$Q_{g(th)}$	Gate Charge at V_{th}		1.3			nC
Q_{oss}	Output Charge	$V_{DS} = 13V, V_{GS} = 0V$	17			nC
$t_{d(on)}$	Turn On Delay Time	$V_{DS} = 12.5V, V_{GS} = 4.5V,$ $I_D = 20A, R_G = 2\Omega$	6.1			ns
t_r	Rise Time		10.7			ns
$t_{d(off)}$	Turn Off Delay Time		12.3			ns
t_f	Fall Time		3.7			ns
Diode Characteristics						
V_{SD}	Diode Forward Voltage	$I_{SD} = 20A, V_{GS} = 0V$	0.8	1		V
Q_{rr}	Reverse Recovery Charge	$V_{DD} = 13V, I_F = 20A, di/dt = 300A/\mu s$	19			nC
t_{rr}	Reverse Recovery Time	$V_{DD} = 13V, I_F = 20A, di/dt = 300A/\mu s$	21			ns

THERMAL CHARACTERISTICS

($T_A = 25^\circ\text{C}$ unless otherwise stated)

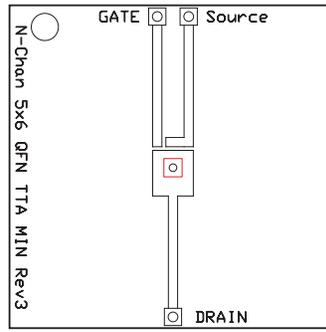
PARAMETER		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case ⁽¹⁾			2.4	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient ^{(1) (2)}			50	$^\circ\text{C}/\text{W}$

- (1) $R_{\theta JC}$ is determined with the device mounted on a 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch x 1.5-inch (3.81-cm x 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. $R_{\theta JC}$ is specified by design, whereas $R_{\theta JA}$ is determined by the user's board design.
- (2) Device mounted on FR4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.



Max $R_{\theta JA} = 50^{\circ}\text{C/W}$
when mounted on
1 inch² (6.45 cm²) of
2-oz. (0.071-mm thick)
Cu.

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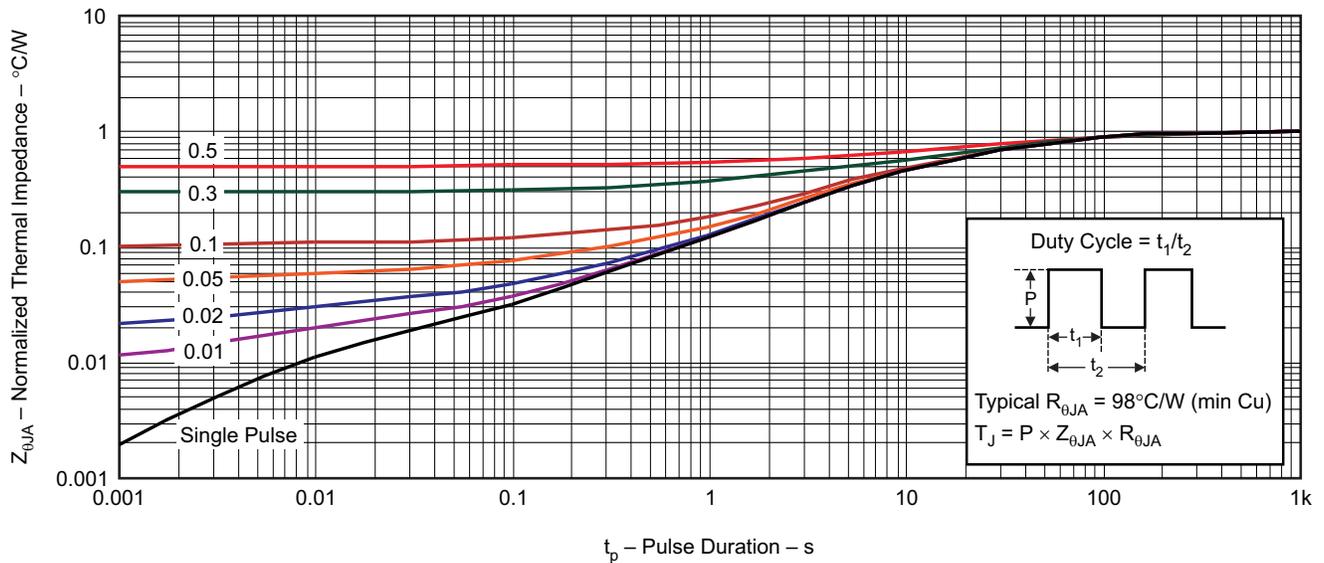


Max $R_{\theta JA} = 123^{\circ}\text{C/W}$
when mounted on
minimum pad area of
2-oz. (0.071-mm thick)
Cu.

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TYPICAL MOSFET CHARACTERISTICS

($T_A = 25^{\circ}\text{C}$ unless otherwise stated)



G012

Figure 1. Transient Thermal Impedance

TYPICAL MOSFET CHARACTERISTICS (continued)

($T_A = 25^\circ\text{C}$ unless otherwise stated)

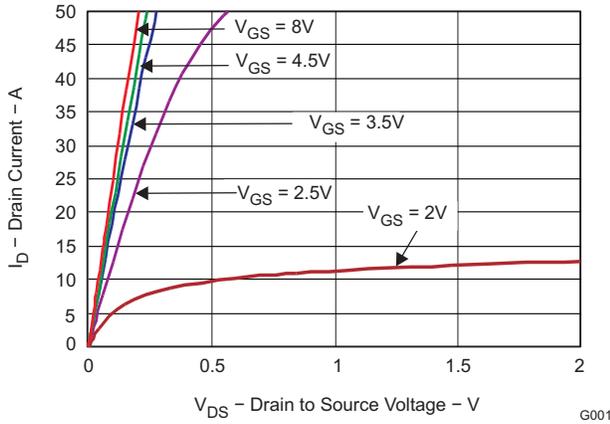


Figure 2. Saturation Characteristics

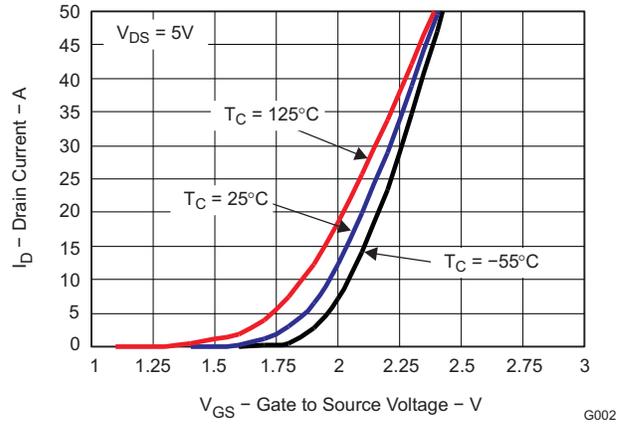


Figure 3. Transfer Characteristics

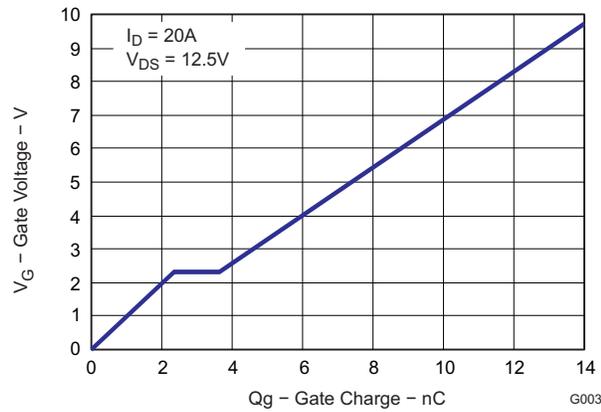


Figure 4. Gate Charge

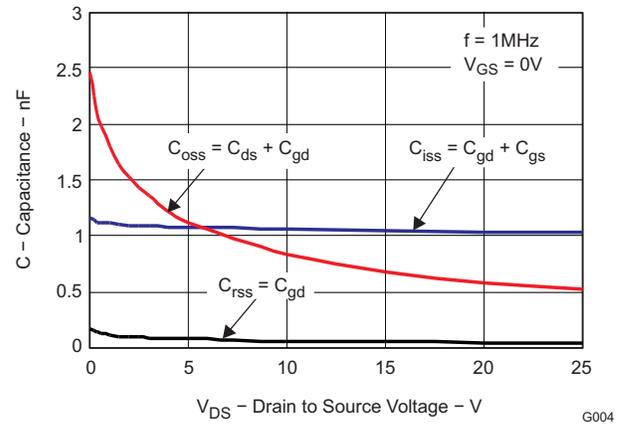


Figure 5. Capacitance

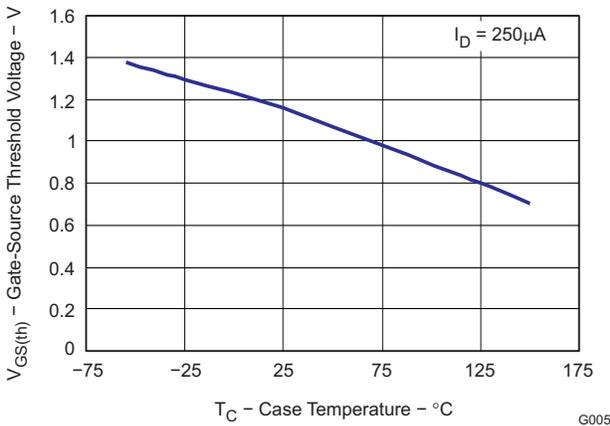


Figure 6. Threshold Voltage vs. Temperature

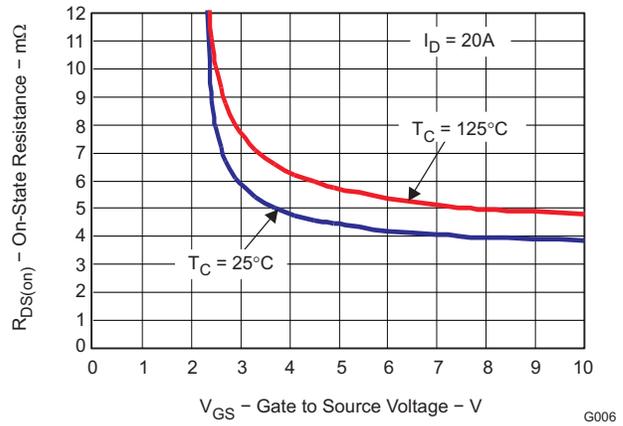


Figure 7. On-State Resistance vs. Gate to Source Voltage

TYPICAL MOSFET CHARACTERISTICS (continued)

($T_A = 25^\circ\text{C}$ unless otherwise stated)

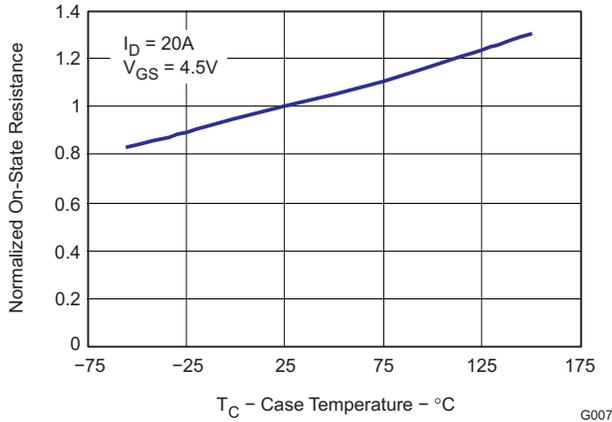


Figure 8. Normalized On-State Resistance vs. Temperature

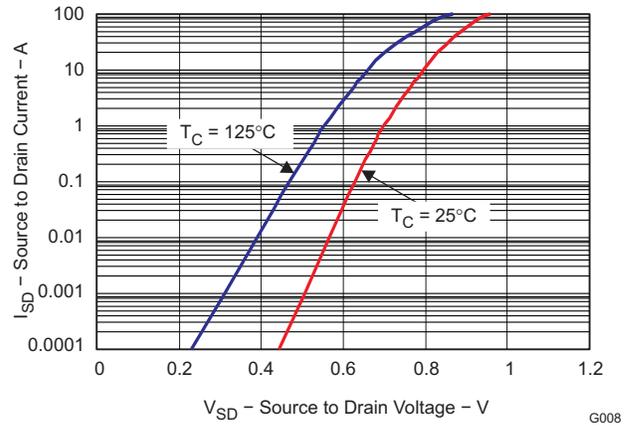


Figure 9. Typical Diode Forward Voltage

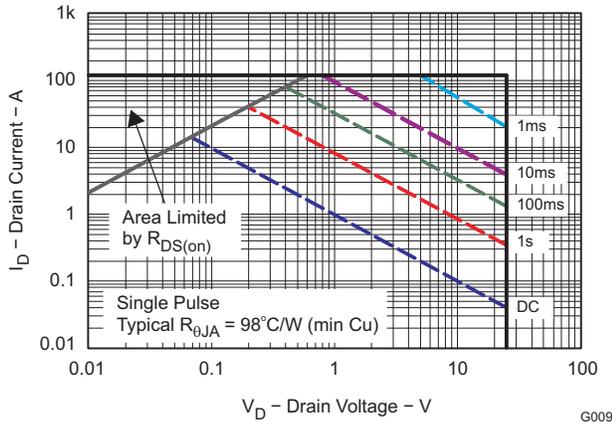


Figure 10. Maximum Safe Operating Area

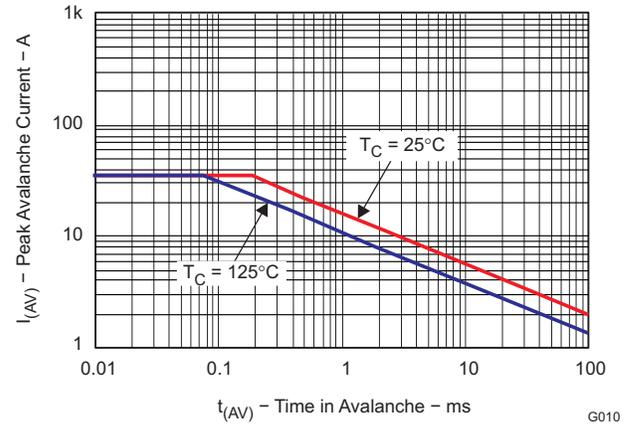


Figure 11. Single Pulse Unclamped Inductive Switching

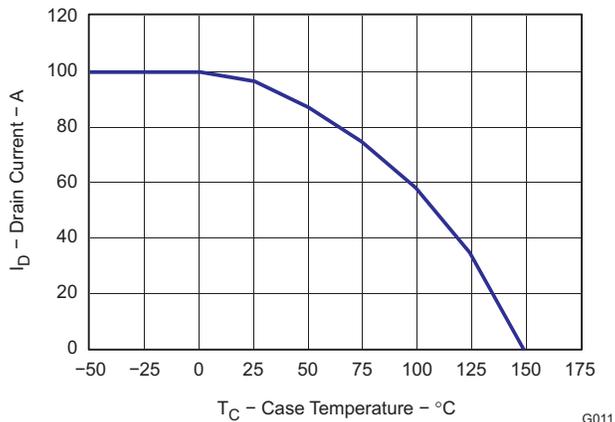
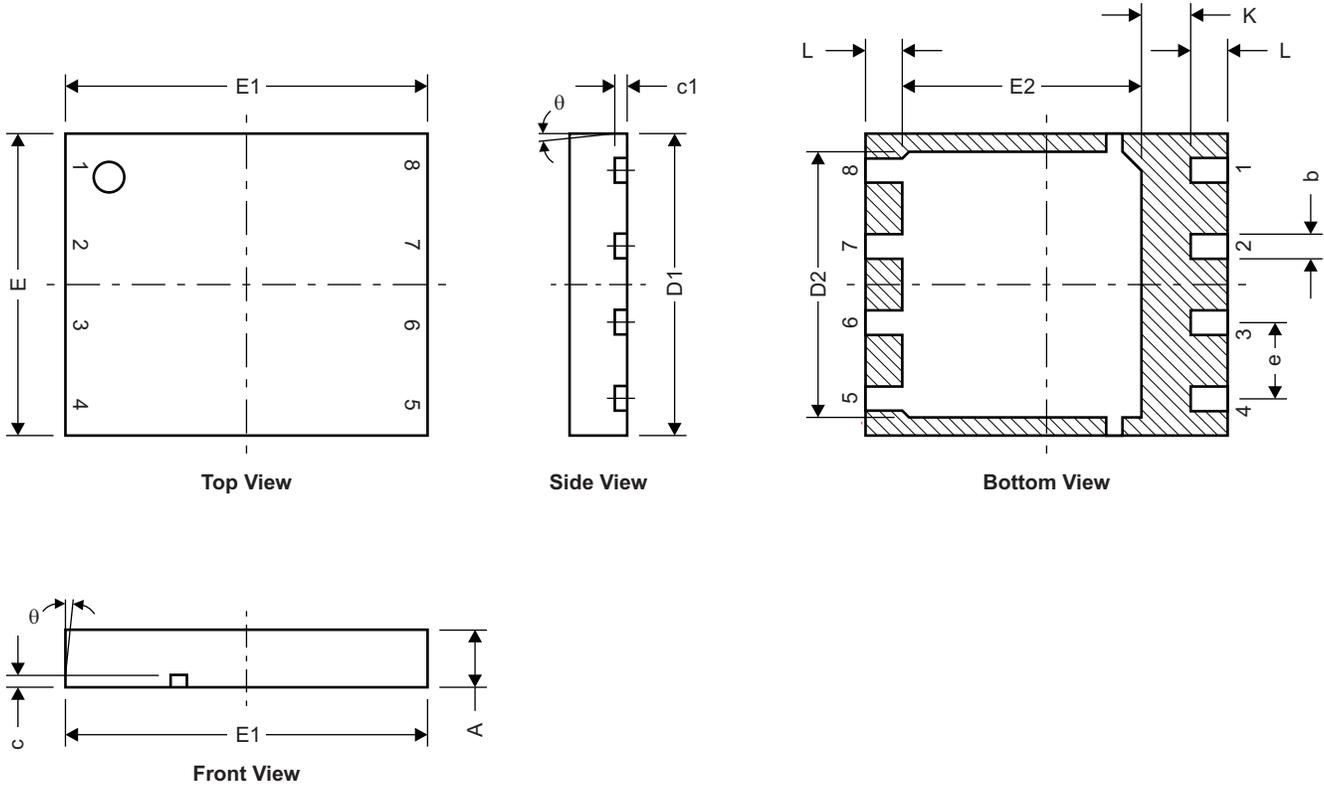


Figure 12. Maximum Drain Current vs. Temperature

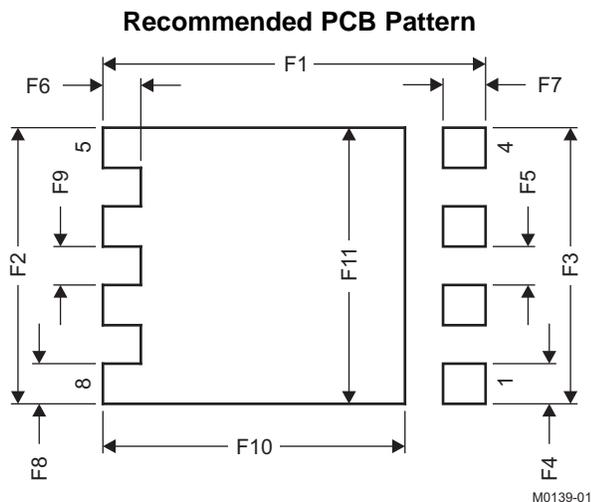
MECHANICAL DATA

Q5 Package Dimensions



M0140-01

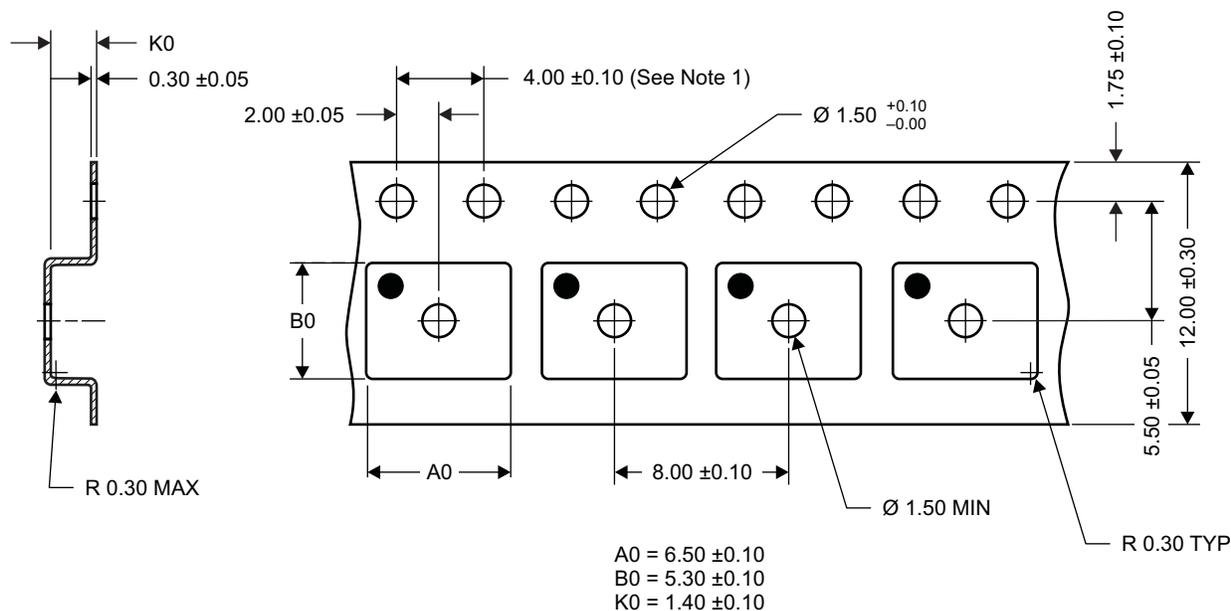
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.950	1.050	0.037	0.039
b	0.360	0.460	0.014	0.018
c	0.150	0.250	0.006	0.010
c1	0.150	0.250	0.006	0.010
D1	4.900	5.100	0.193	0.201
D2	4.320	4.520	0.170	0.178
E	4.900	5.100	0.193	0.201
E1	5.900	6.100	0.232	0.240
E2	3.920	4.12	0.154	0.162
e	1.27 TYP		0.050	
K	0.760		0.030	
L	0.510	0.710	0.020	0.028
θ	0.00			



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
F1	6.205	6.305	0.244	0.248
F2	4.460	4.560	0.176	0.180
F3	4.460	4.560	0.176	0.180
F4	0.650	0.700	0.026	0.028
F5	0.620	0.670	0.024	0.026
F6	0.630	0.680	0.025	0.027
F7	0.700	0.800	0.028	0.031
F8	0.650	0.700	0.026	0.028
F9	0.620	0.670	0.024	0.026
F10	4.900	5.000	0.193	0.197
F11	4.460	4.560	0.176	0.180

For recommended circuit layout for PCB designs, see application note [SLPA005 – Reducing Ringing Through PCB Layout Techniques](#).

Q5 Tape and Reel Information



Notes:

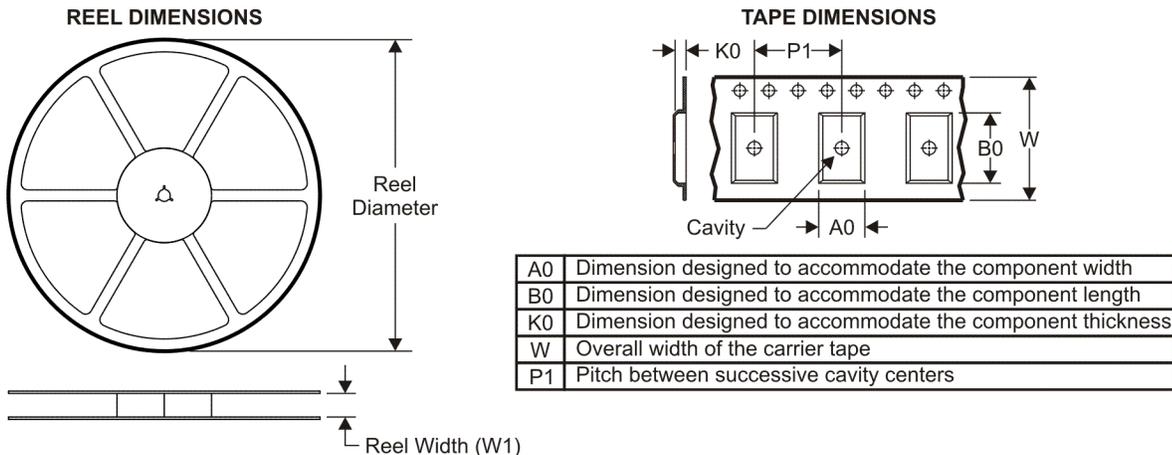
- 10-sprocket hole-pitch cumulative tolerance ±0.2
- Camber not to exceed 1mm in 100mm, noncumulative over 250mm
- Material: black static-dissipative polystyrene
- All dimensions are in mm, unless otherwise specified.
- A0 and B0 measured on a plane 0.3mm above the bottom of the pocket
- MSL1 260°C (IR and convection) PbF reflow compatible

REVISION HISTORY

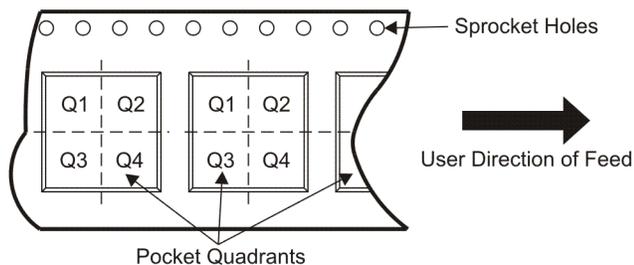
Changes from Original (August 2009) to Revision A	Page
• Changed Note1 of the ABSOLUTE MAXIMUM RATINGS From: $R_{\theta JA} = 39^{\circ}\text{C/W}$ To: Typical $R_{\theta JA} = 39^{\circ}\text{C/W}$	1
• Changed Figure 1 text From: $R_{\theta JA} = 99^{\circ}\text{C/W}$ To: Typical $R_{\theta JA} = 98^{\circ}\text{C/W}$	3
• Changed Figure 10 text From: $R_{\theta JA} = 99^{\circ}\text{C/W}$ To: Typical $R_{\theta JA} = 98^{\circ}\text{C/W}$	5
• Changed Figure 11 X- axis values	5

Changes from Revision A (April 2010) to Revision B	Page
• Changed $R_{DS(on)} - V_{GS} = 3\text{V}$ in the Electrical Characteristics table From: 7 To: 7.2 in the max column	2
• Deleted the Package Marking Information section	7

TAPE AND REEL INFORMATION



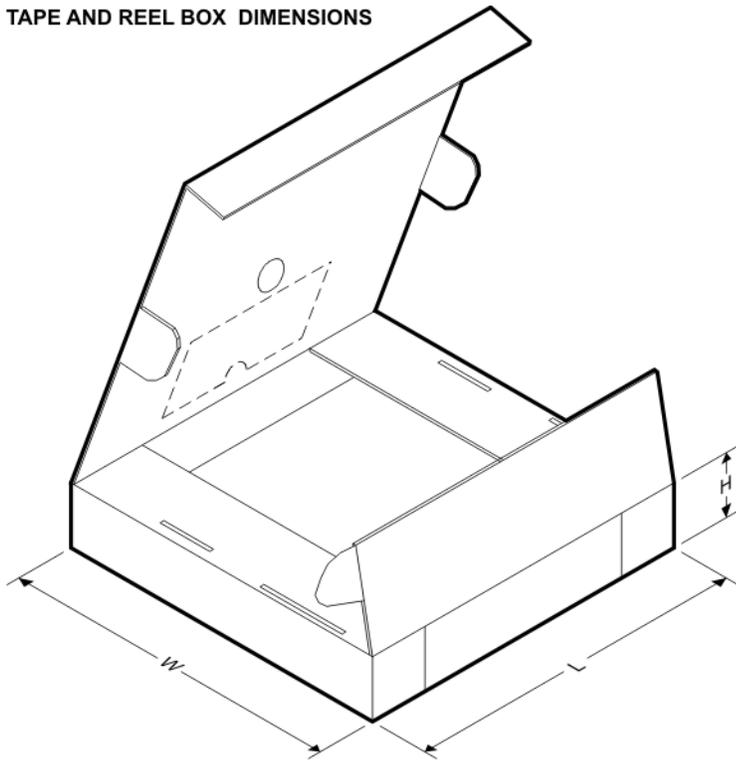
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD16322Q5	SON	DQH	8	2500	330.0	12.8	6.5	5.3	1.4	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD16322Q5	SON	DQH	8	2500	335.0	335.0	32.0

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